



AMP5059P

SOLID STATE HIGH POWER PULSE AMPLIFIER

FEATURES

- Class AB linear GaN hybrid design
- Designed for narrow X-Band high power pulse applications
- Solid-State Amplifier for TWT Driver
- Built-in protection circuits
- High reliability and ruggedness

ELECTRICAL SPECIFICATIONS: 50Ω, 25°C

Parameter	Specification			Notes	
Operating Frequency Range	12 ±0.1 GHz				
Peak Pulse Output Power	400 Watt Min				
Pulse Characteristics	Width	Duty	PRF	Rise / Fall	
	2 μS	-	10 Hz	75 nS Max	
Power Gain	56 dB Min				
Input Return Loss	-14 dB Max			Relative to 50 Ohm	
Harmonics	-30 dBc Typ			At rated Pout	
Spurious	-60 dBc Max			Non-harmonics	
Operating Voltage	42 VDC Nom				
Current Consumption	3.5 Amp Avg			2 μS at rated Pout	
Input Power Protection	+6 dBm Max			<10 Sec without damage	
Load VSWR Protection	∞ : 1			Output Isolator	

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Case Temperature	-20 to +75 °C	
Storage Temperature	-40 to +85 °C	
Relative Humidity	5 to 95 %	Non-condensing

MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions	220 x 235 x 45 mm	Excluding Connectors
Weight	-	
RF Connectors In/Out	SMA-F / Hi Power Type-N	Optional Waveguide
DC Power / Interface Connector	Hybrid D-Sub	
Cooling	External Heatsink	Forced air required

D-SUB CONNECTOR PIN ASSIGNMENT

Pin	Function	Description
1	FWD	N/C
2	REV	N/C
3	CURRENT MONITOR	I _D @20mV/100mA Typ
4	TEMP SENSOR	V _T @10mV/°C + 500mV Typ
5	SHUTDOWN	Enable = TTL "Hi" or Open; Disable = TTL "Lo" or Short
A1	VDD	42VDC
A2	GND	Ground



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OUTLINE DRAWING